



GP
ELECTRONICS

MMBT3904M

MMBT3904M Transistor(NPN)

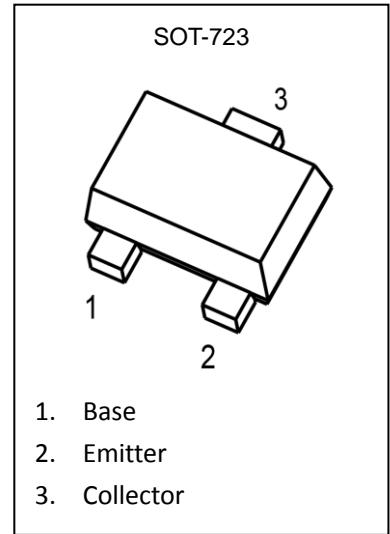
Feature

- Switching Transistor
- Collector-emitter voltage $V_{CE}=40V$
- Collector current $I_C=0.2A$

Marking: 1N

MAXIMUM RATINGS ($T_a=25^\circ C$ unless otherwise noted)

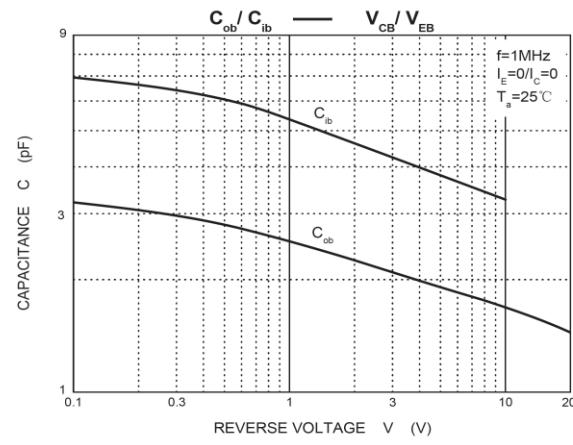
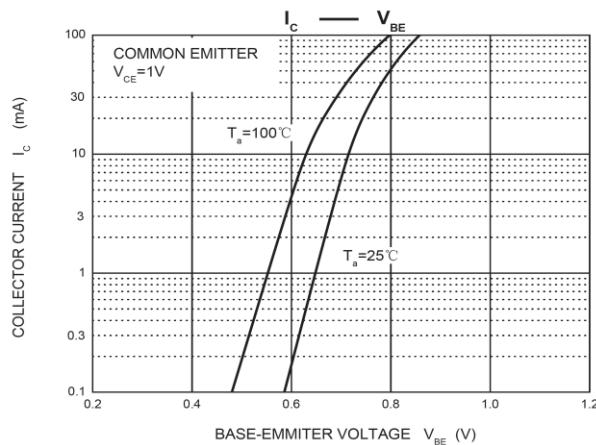
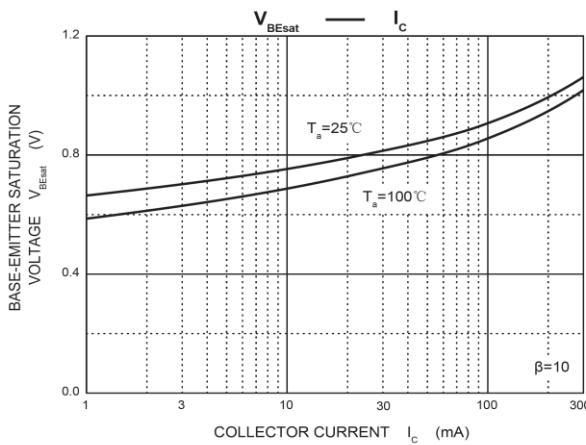
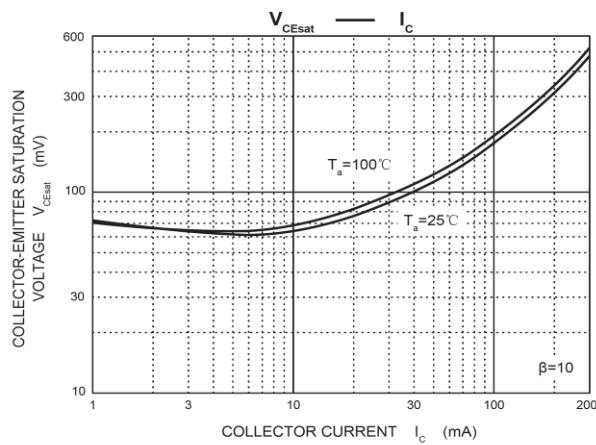
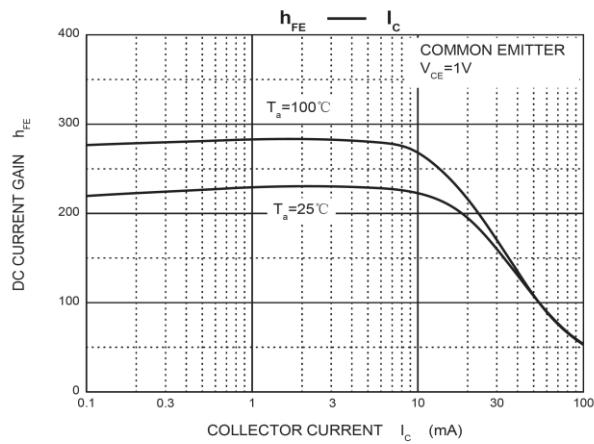
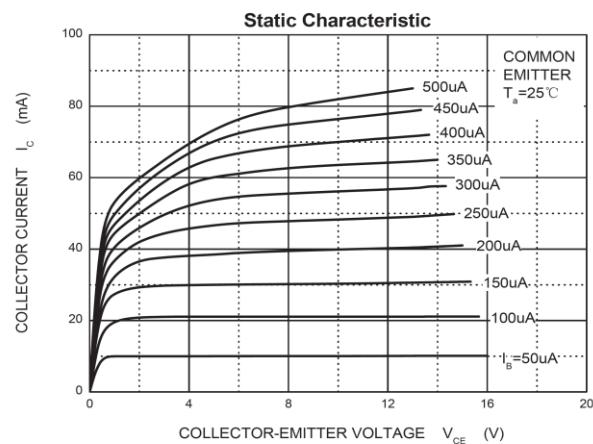
Parameter	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	60	V
Collector-Emitter Voltage	V_{CEO}	40	V
Emitter-Base Voltage	V_{EBO}	6	V
Collector Current -Continuous	I_C	0.2	A
Power Dissipation	P_d	0.1	W
Junction Temperature	T_J	150	$^\circ C$
Storage Temperature	T_{STG}	-55~ +150	$^\circ C$

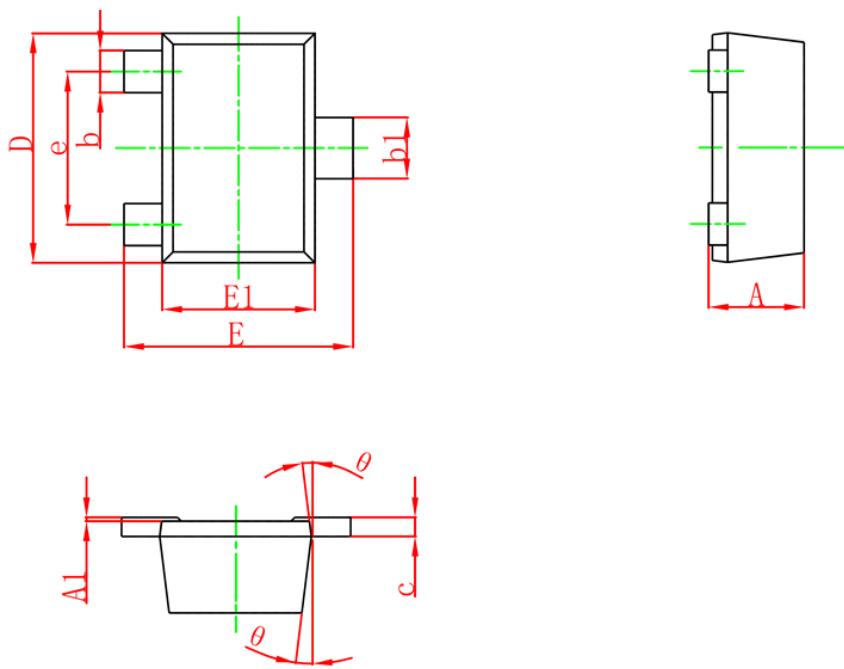


ELECTRICAL CHARACTERISTICS($T_a=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=10\mu A, I_E=0$	60		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1mA, I_B=0$	40		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=10\mu A, I_C=0$	6		V
Collector cut-off current	I_{CBO}	$V_{CB}=60V, I_E=0$		100	nA
Collector cut-off current	I_{CEX}	$V_{CE}=30V, V_{EB(off)}=3V$		50	nA
Baes cut-off current	I_{BEX}			50	nA
Emitter cut-off current	I_{EBO}	$V_{EB}=5V, I_C=0$		100	nA
DC current gain	h_{FE1}	$V_{CE}=1V, I_C=0.1mA$	40		
	h_{FE2}	$V_{CE}=1V, I_C=1mA$	70		
	h_{FE3}	$V_{CE}=1V, I_C=10mA$	100	300	
	h_{FE4}	$V_{CE}=1V, I_C=50mA$	60		
	h_{FE5}	$V_{CE}=1V, I_C=100mA$	30		
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=50mA, I_B=0mA$		0.3	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=50mA, I_B=0mA$		0.95	V
Transition frequency	f_T	$V_{CE}= 20V, I_C=10mA, f=100MHz$	300		MHZ

Typical Characteristics



SOT-723 Package Information


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.400	0.500	0.016	0.020
A1	0.000	0.050	0.000	0.002
b	0.150	0.270	0.006	0.011
b1	0.200	0.370	0.008	0.015
c	0.060	0.160	0.002	0.006
D	1.100	1.300	0.043	0.051
E	1.100	1.300	0.043	0.051
E1	0.700	0.900	0.028	0.035
e	0.8TYP		0.031TYP	
θ	8°REF		8°REF	